

## Silicon Power Schottky Diode

$V_{RRM} = 45\text{ V} - 100\text{ V}$

$I_F = 35\text{ A}$

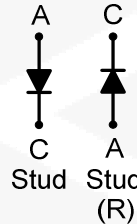
### Features

- High Surge Capability
- Types from 45 V to 100 V  $V_{RRM}$
- Not ESD Sensitive

### Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.

DO-4 Package



Maximum ratings, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)

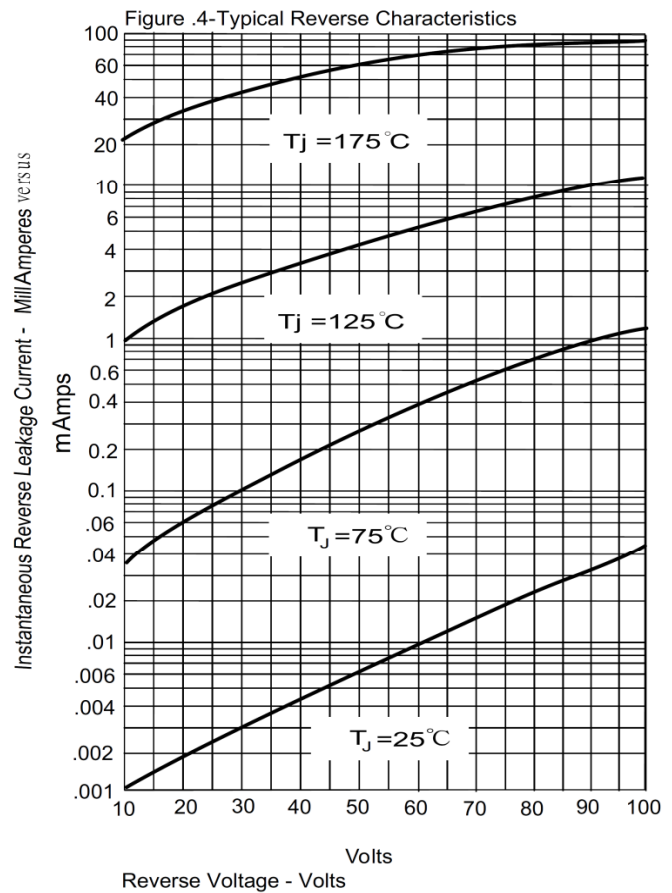
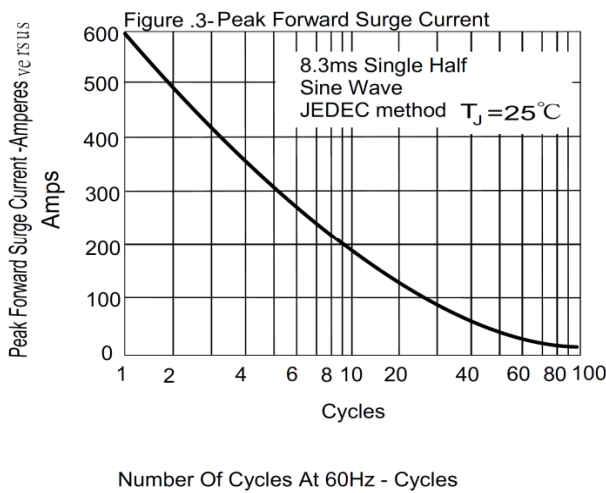
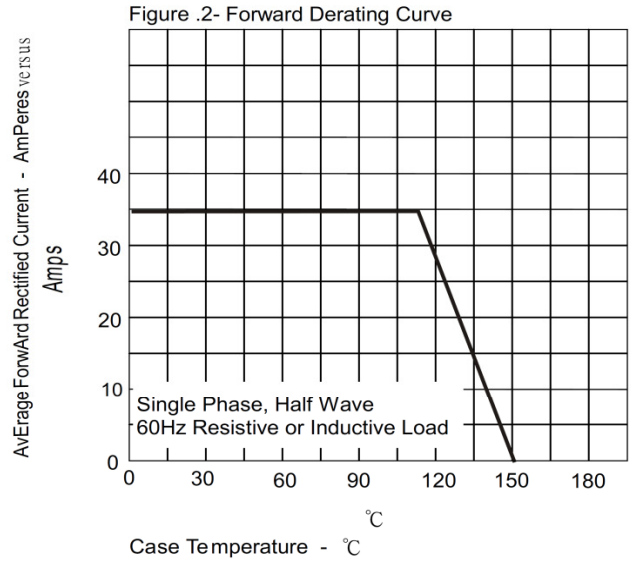
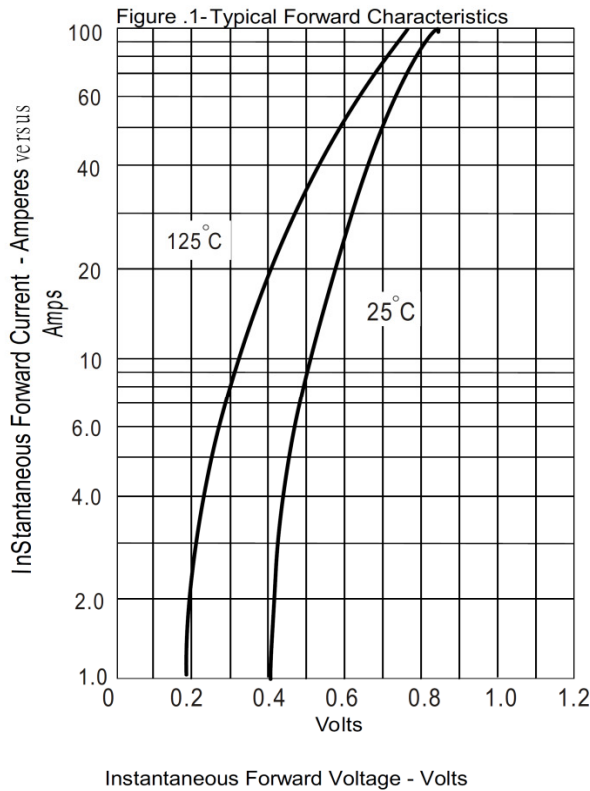
| Parameter  | Symbol     | Conditions   | MBR3545(R) | MBR3560(R) | MBR3580(R) | MBR35100(R) | Unit             |
|--|------------|--|------------|------------|------------|-------------|------------------|
| Repetitive peak reverse voltage                      | $V_{RRM}$  |  | 45         | 60         | 80         | 100         | V                |
| RMS reverse voltage                                  | $V_{RMS}$  |  | 32         | 42         | 57         | 70          | V                |
| DC blocking voltage                                  | $V_{DC}$   |  | 45         | 60         | 80         | 100         | V                |
| Continuous forward current                           | $I_F$      | $T_C \leq 110\text{ }^\circ\text{C}$                     | 35         | 35         | 35         | 35          | A                |
| Surge non-repetitive forward current, Half Sine Wave | $I_{F,SM}$ | $T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$ | 600        | 600        | 600        | 600         | A                |
| Operating temperature                                | $T_j$      |  | -55 to 150 | -55 to 150 | -55 to 150 | -55 to 150  | $^\circ\text{C}$ |
| Storage temperature                                  | $T_{stg}$  |  | -55 to 150 | -55 to 150 | -55 to 150 | -55 to 150  | $^\circ\text{C}$ |

Electrical characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter             | Symbol | Conditions  | MBR3545(R) | MBR3560(R) | MBR3580(R) | MBR35100(R) | Unit |
|-----------------------|--------|---|------------|------------|------------|-------------|------|
| Diode forward voltage | $V_F$  | $I_F = 35\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$  | 0.68       | 0.75       | 0.84       | 0.84        | V    |
| Reverse current       | $I_R$  | $V_R = 20\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$  | 1.5        | 1.5        | 1.5        | 1.5         | mA   |
|                       |        | $V_R = 20\text{ V}$ , $T_j = 125\text{ }^\circ\text{C}$ | 25         | 25         | 25         | 25          |      |

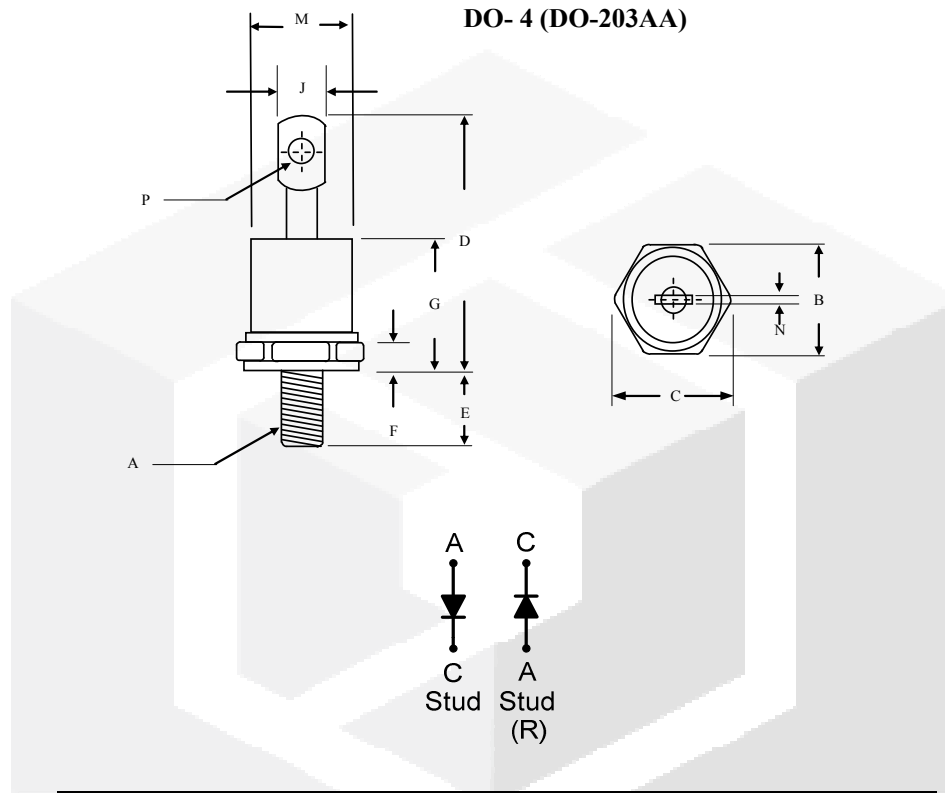
### Thermal characteristics

| Parameter                           | Symbol     | Conditions | MBR3545(R) | MBR3560(R) | MBR3580(R) | MBR35100(R) | Unit               |
|-------------------------------------|------------|------------|------------|------------|------------|-------------|--------------------|
| Thermal resistance, junction - case | $R_{thJC}$ |            | 1.5        | 1.5        | 1.5        | 1.5         | $^\circ\text{C/W}$ |



## Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



|   | Inches    |        | Millimeters |       |
|---|-----------|--------|-------------|-------|
|   | Min       | Max    | Min         | Max   |
| A | 10-32 UNF |        |             |       |
| B | 0.424     | 0.437  | 10.77       | 11.10 |
| C | -----     | 0.505  | -----       | 12.82 |
| D | -----     | 0.800  | -----       | 20.30 |
| E | 0.453     | 0.492  | 11.50       | 12.50 |
| F | 0.114     | 0.140  | 2.90        | 3.50  |
| G | -----     | 0.405  | -----       | 10.29 |
| J | -----     | 0.216  | -----       | 5.50  |
| M | -----     | φ0.302 | -----       | φ7.68 |
| N | 0.031     | 0.045  | 0.80        | 1.15  |
| P | 0.070     | 0.79   | 1.80        | 2.00  |